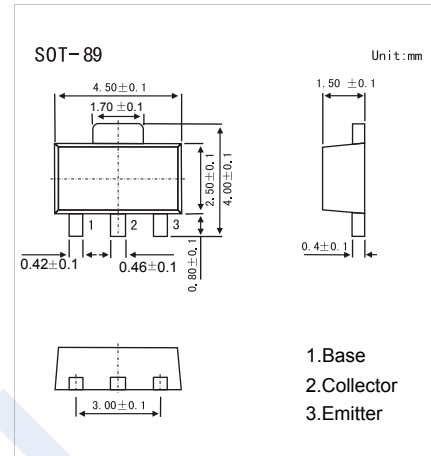


PNP Transistors

2SB1118

■ Features

- Low collector-to-emitter saturation voltage.
- Very small size making it easy to provide high density, small-sized hybrid IC's.
- Complementary to 2SD1618



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-20	V
Collector - Emitter Voltage	V _{CEO}	-15	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-0.7	A
Collector current -Pulse	I _{CP}	-1.5	
Collector Power Dissipation (Note.1)	P _C	0.5 1.3	W
Junction Temperature	T _J	150	
Storage Temperature range	T _{stg}	-55 to 150	°C

Note.1: Mounted on ceramic board (250mm² × 0.8mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E = 0	-20			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} = ∞	-15			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -15V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -5 mA, I _B = -0.5mA		-15	-35	mV
		I _C = -100 mA, I _B = -10mA		-60	-120	
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -100 mA, I _B = -10mA		-0.8	-1.2	V
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -50 mA	140		560	
		V _{CE} = -2V, I _C = -500 mA	60			
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		13		pF
Transition frequency	f _t	V _{CE} = -10V, I _C = -50mA		250		MHz

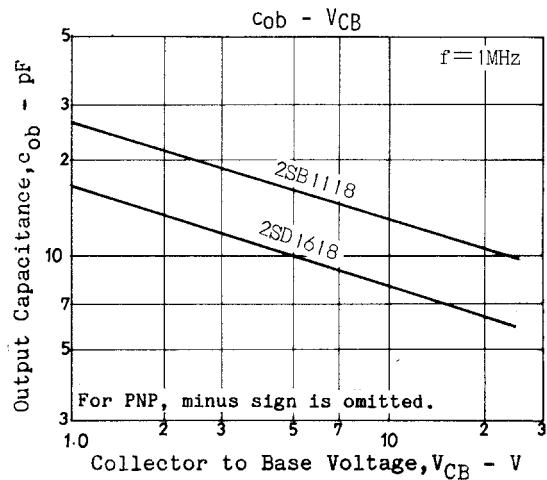
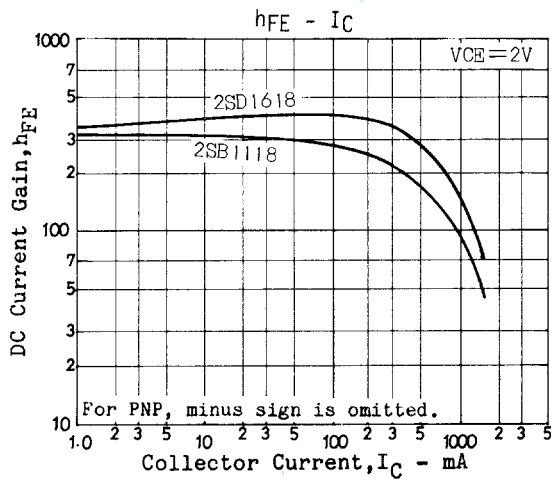
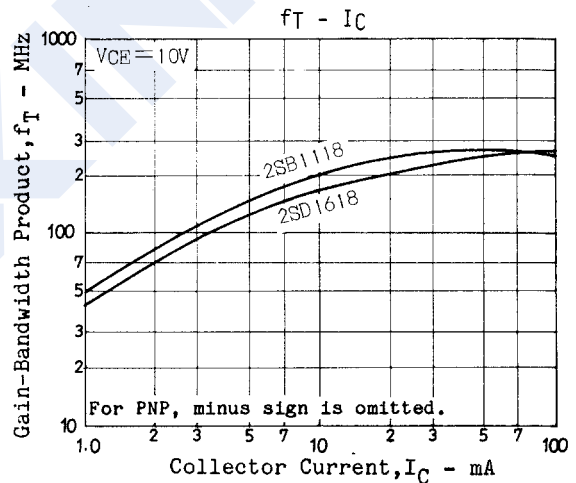
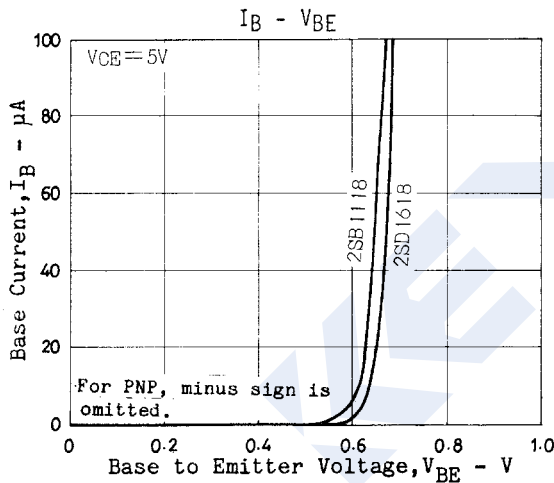
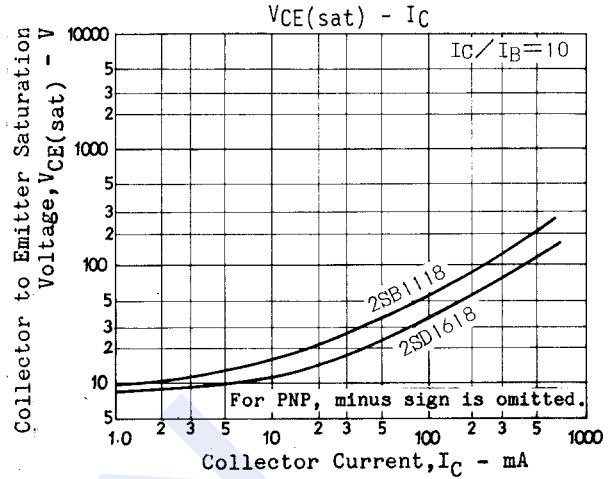
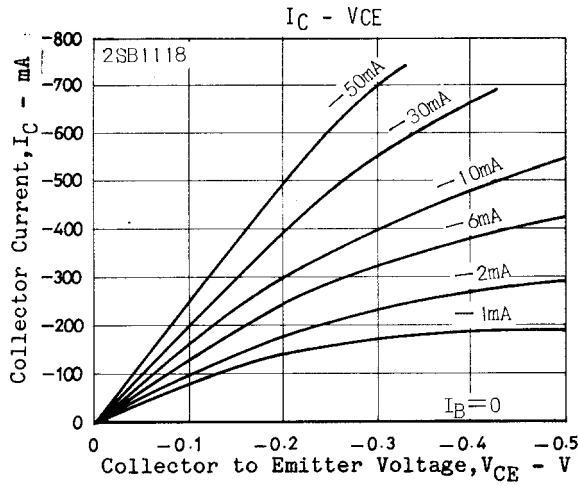
■ Classification of h_{FE}(1)

Type	2SB1118-S	2SB1118-T	2SB1118-U
Range	140-280	200-400	280-560
Marking	BA S*	BA T*	BA U*

PNP Transistors

2SB1118

■ Typical Characteristics



PNP Transistors

2SB1118

■ Typical Characteristics

